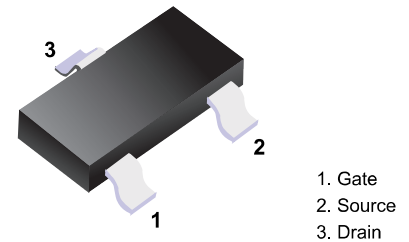


■ N-Channel Enhancement Mode
Product Summary

BVDSS	RDSON	ID
60V	110mΩ	2.1A


General Description

The WST6066A is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

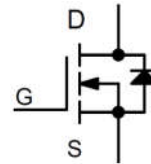
The WST6066A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

■ Simplified outline(SOT23-3L)

■ Marking Code: 6066A
Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	2.1	A
$I_D@T_C=70^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	1.5	A
I_{DM}	Pulsed Drain Current ²	10	A
EAS	Single Pulse Avalanche Energy ³	15	mJ
I_{AS}	Avalanche Current	21	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	1.25	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	25	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	55	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.041	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =2.1A	---	85	110	mΩ
		V _{GS} =2.5V, I _D =1.5A	---	95	120	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.5	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.7	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =44V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =44V, V _{GS} =0V, T _J =85°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =4A	---	10	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.5	5	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =27V, V _{GS} =4.5V, I _D =2.1A	---	2.1	3.9	nC
Q _{gs}	Gate-Source Charge		---	0.6	---	
Q _{gd}	Gate-Drain Charge		---	0.8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =27V, V _{GS} =10V, R _G =6Ω I _D =1A	---	3.6	---	ns
T _r	Rise Time		---	3.5	---	
T _{d(off)}	Turn-Off Delay Time		---	32	---	
T _f	Fall Time		---	3	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	295	---	pF
C _{oss}	Output Capacitance		---	40	---	
C _{rss}	Reverse Transfer Capacitance		---	15	---	

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =25V, L=0.1mH, I _{AS} =15A	15.2	---	---	mJ

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V, Force Current	---	---	1	A
I _{SM}	Pulsed Source Current ^{2,6}		---	---	4	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =4A, di/dt=100A/μs, T _J =25°C	---	10.1	---	nS
Q _{rr}	Reverse Recovery Charge		---	6.4	---	nC

Note :

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10sec.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=15A
- The power dissipation is limited by 150°C junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

TYPICAL CHARACTERISTICS (25°C Unless Note)

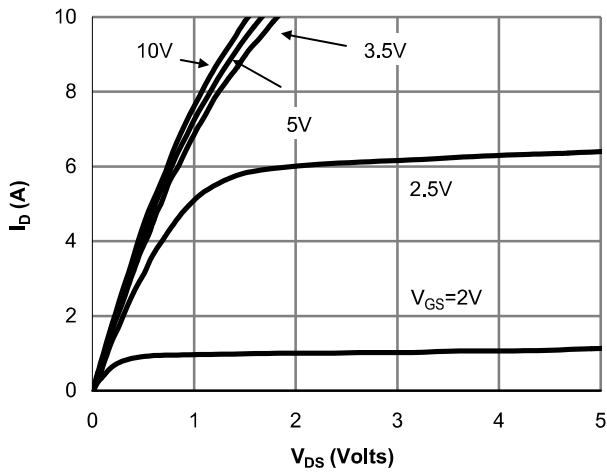


Fig 1: On-Region characteristics

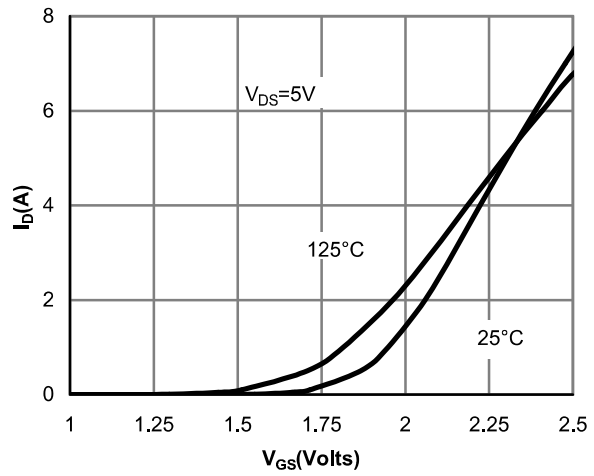


Figure 2: Transfer Characteristics

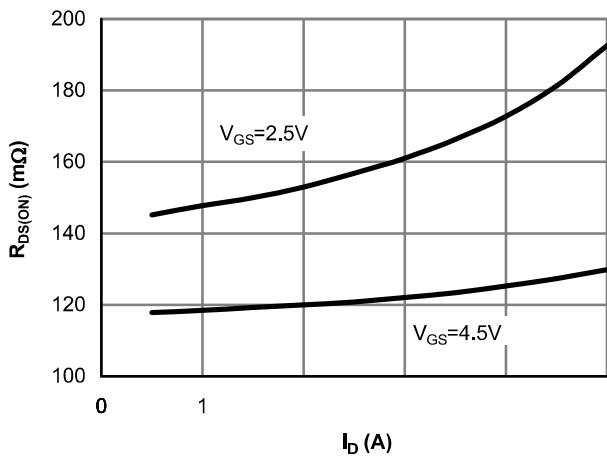


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

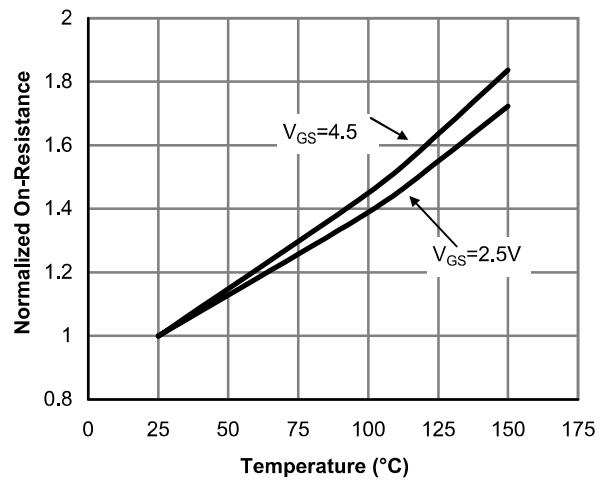


Figure 4: On-Resistance vs. Junction Temperature

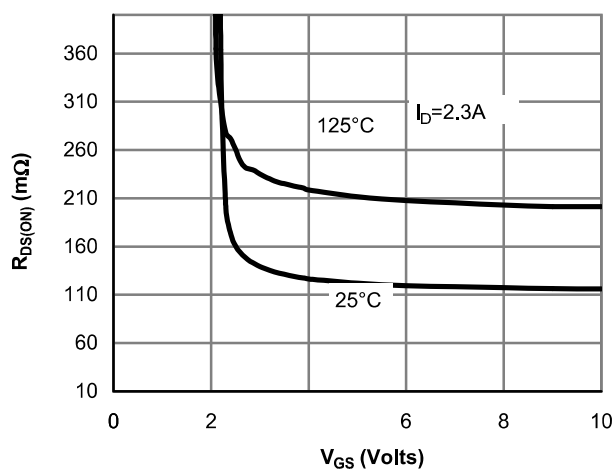


Figure 5: On-Resistance vs. Gate-Source Voltage

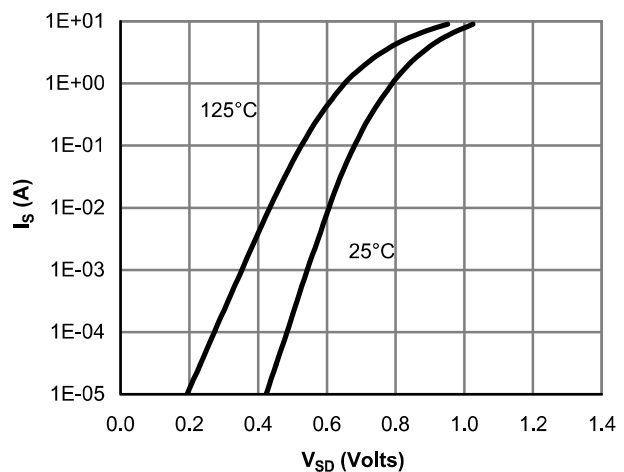


Figure 6: Body-Diode Characteristics

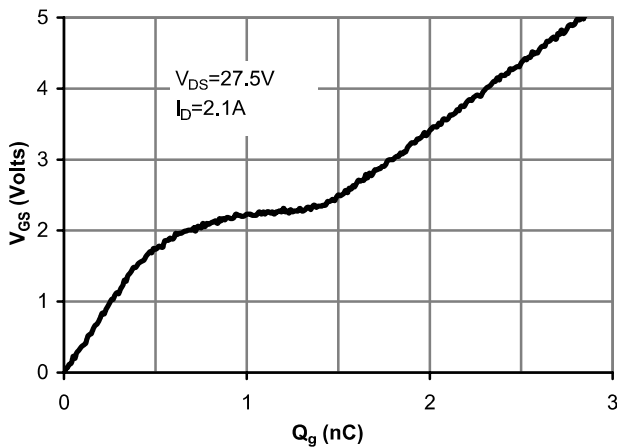


Figure 7: Gate-Charge Characteristics

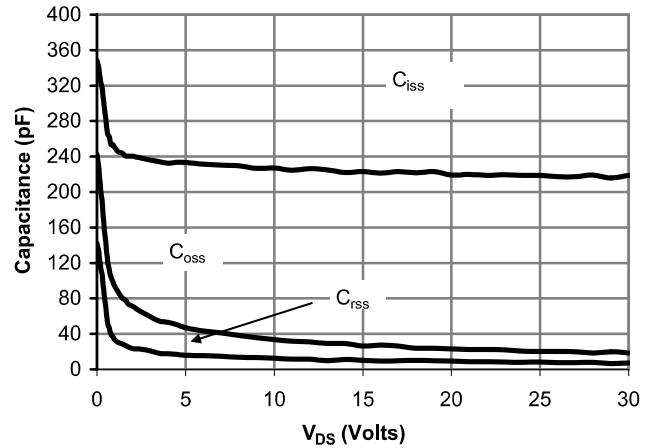


Figure 8: Capacitance Characteristics

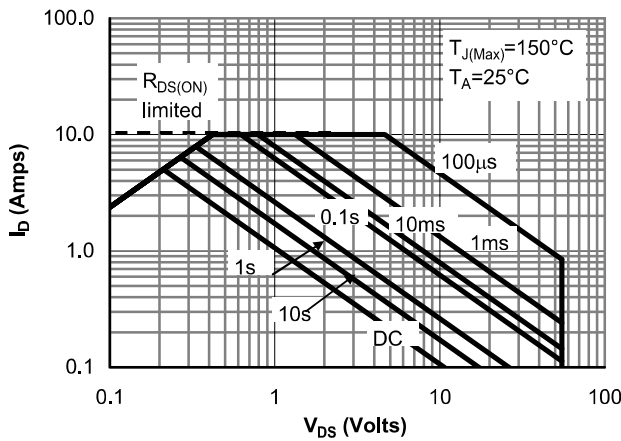


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

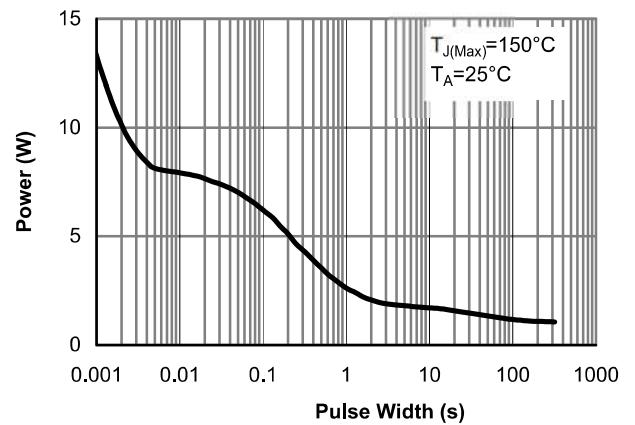


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

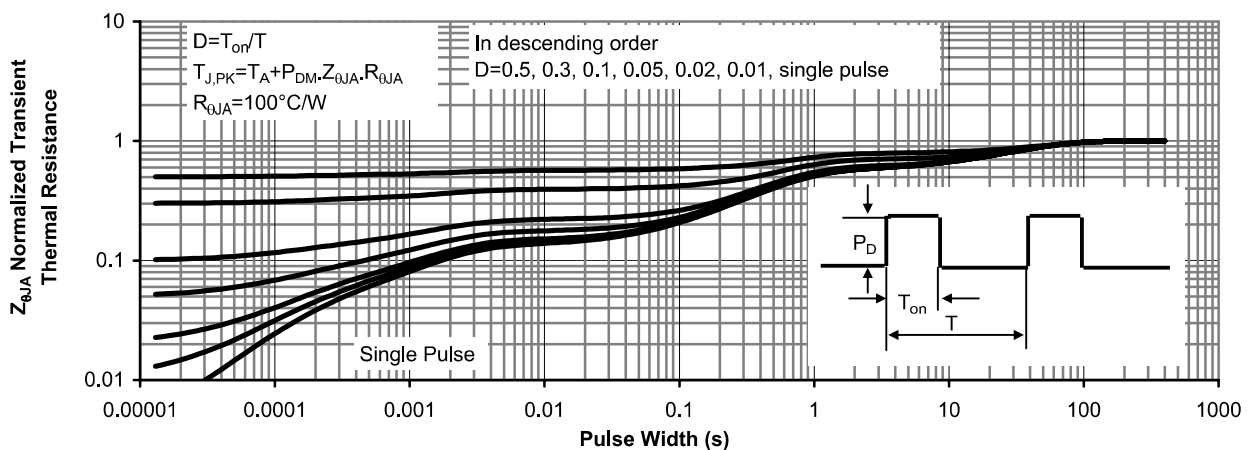
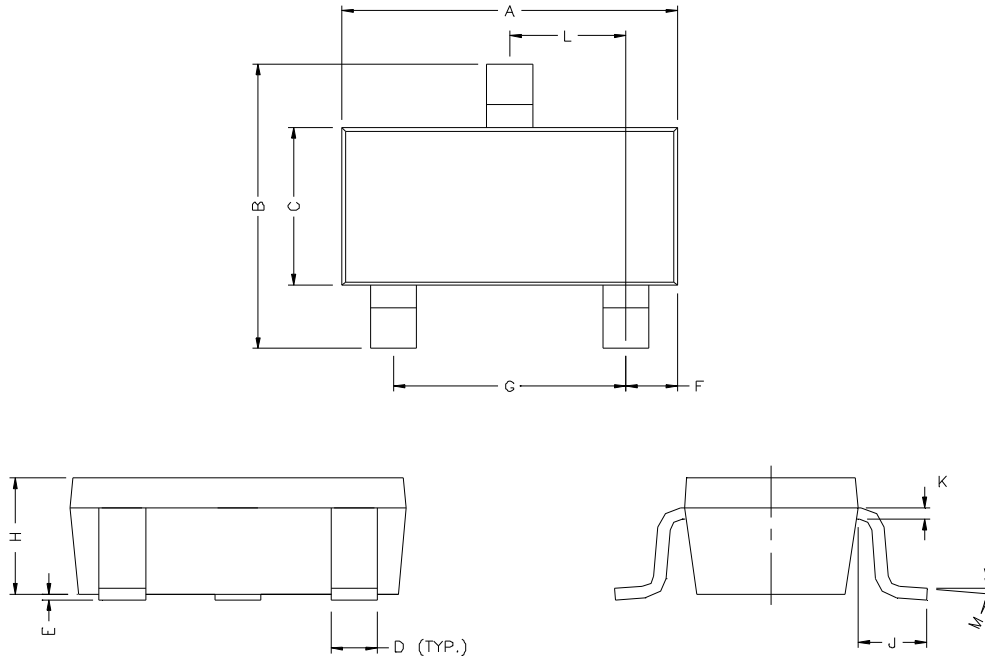


Figure 11: Normalized Maximum Transient Thermal Impedance

Package Outline

SOT23-3L



DIMENSIONS (mm are the original dimensions)

UNIT	A	B	C	D	E	F	G	H	K	J	L	M
mm	2.70 3.10	2.65 2.95	1.50 1.70	0.35 0.50	0 0.10	0.45 0.55	1.9	1.00 1.30	0.10 0.20	0.40 -	0.85 1.15	0° 10°

Summary of Packing Options

Package	Package Description	Packing Quantity	Industry Standard
SOT23-3L	Tape/Reel, 7" reel	3000	EIA-481-1